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DOT MATRIX DIGIT LED DISPLAY (0.7Inch)



Lead-Free Parts

## LMD5702BEGR-XX-PF

# DATA SHEET

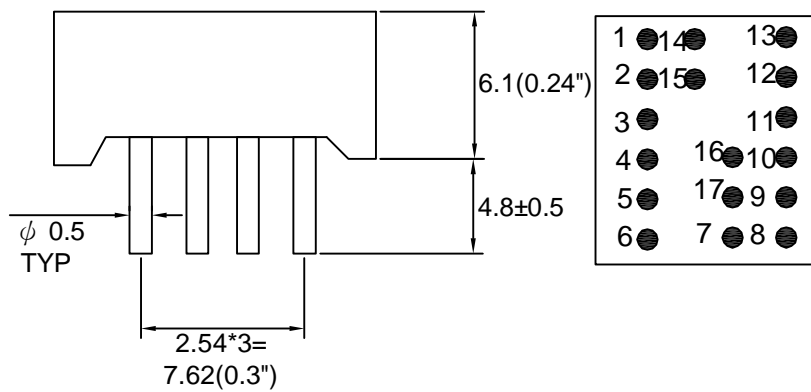
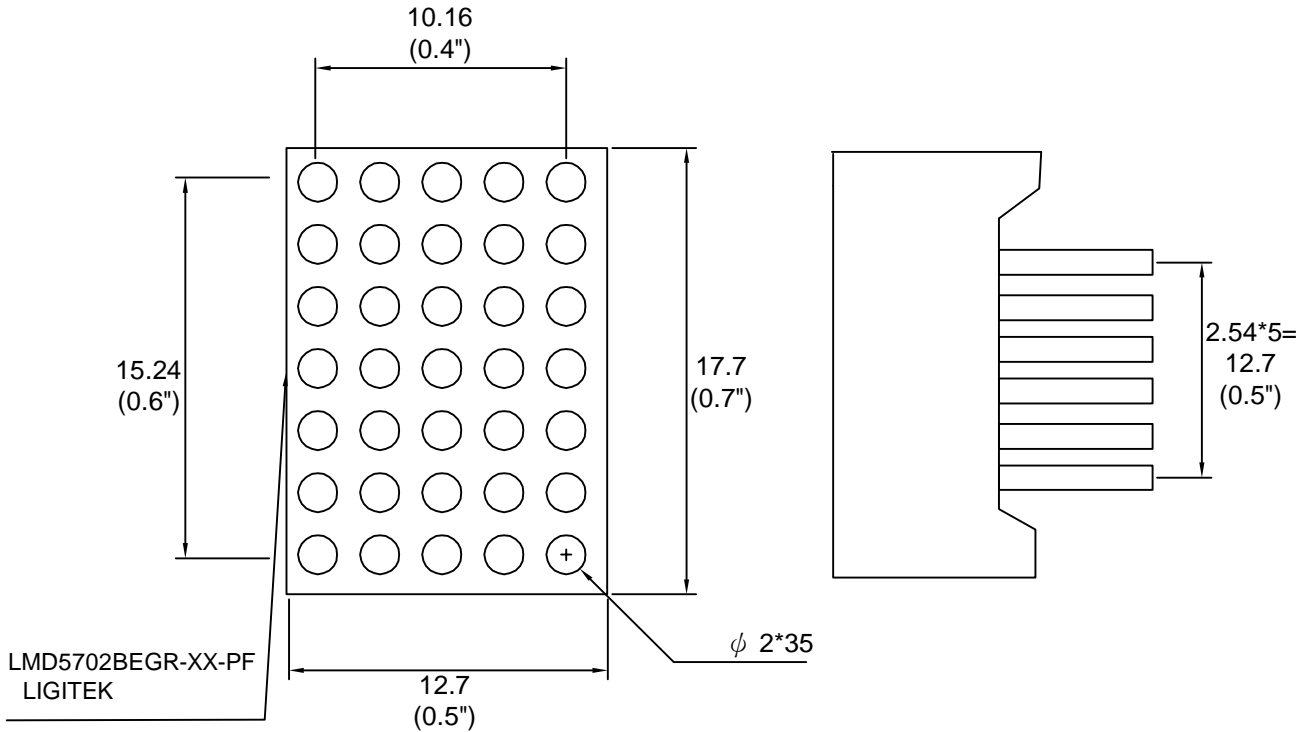
DOC. NO : QW0905-LMD5702BEGR-XX-PF

REV. : A

DATE : 21 - Feb. - 2008



### Package Dimensions



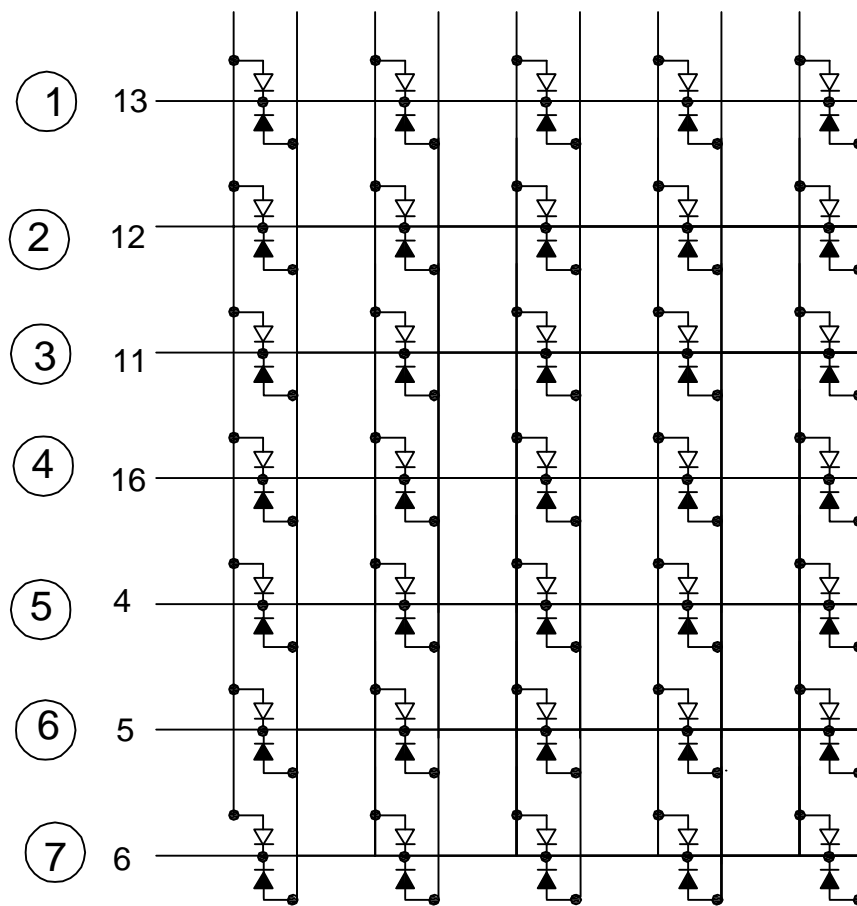
Note : 1.All dimension are in millimeters and (Inch) tolerance is  $\pm 0.25$ mm unless otherwise noted.  
2.Specifications are subject to change without notice.



Internal Circuit Diagram

LMD5702BXXR-XX-PF

COLUMN	—	①	②	③	④	⑤
ROW PIN	—	3 2	1 15	14 17	7 9	8 10



▼	▽
GREEN	RED



### Electrical Connection

PIN NO.	LMD5702BEGR-XX-PF	PIN NO.	LMD5702BEGR-XX-PF
1	Anode Column 2 (Red)	10	Anode Column 5 (Green)
2	Anode Column 1 (Green)	11	Cathode Row 3
3	Anode Column 1 (Red)	12	Cathode Row 2
4	Cathode Row 5	13	Cathode Row 1
5	Cathode Row 6	14	Anode Column 3 (Red)
6	Cathode Row 7	15	Anode Column 2 (Green)
7	Anode Column 4 (Red)	16	Cathode Row 4
8	Anode Column 5 (Red)	17	Anode Column 3 (Green)
9	Anode Column 4 (Green)		

**Absolute Maximum Ratings at Ta=25 °C**

Parameter	Symbol	Ratings		UNIT
		E	G	
Forward Current Per Chip	IF	30	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	120	120	mA
Power Dissipation Per Chip	PD	100	100	mW
Reverse Current Per Any Chip	Ir	10		$\mu$ A
Operating Temperature	Topr	-25 ~ +85		°C
Storage Temperature	Tstg	-25 ~ +85		°C
Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260 °C				

**Part Selection And Application Information(Ratings at 25°C)**

PART NO	CHIP		common cathode or anode	$\lambda$ P (nm)	$\Delta \lambda$ (nm)	Electrical					IV-M
	Material	Emitted				Vf(v)			Iv(mcd)		
						Min.	Typ.	Max.	Min.	Typ.	
LMD5702BEGR-XX-PF	GaAsP/GaP	Orange	Common Anode	640	45	1.7	2.1	2.6	3.05	5.0	2:1
	GaP	Green		565	30	1.7	2.1	2.6	5.0	8.5	

Note : 1.The forward voltage data did not including  $\pm 0.1V$  testing tolerance.  
 2. The luminous intensity data did not including  $\pm 15\%$  testing tolerance.

**Test Condition For Each Parameter**

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	V <sub>f</sub>	volt	I <sub>f</sub> =20mA
Luminous Intensity Per Chip	I <sub>v</sub>	mcd	I <sub>f</sub> =10mA
Peak Wavelength	λ <sub>p</sub>	nm	I <sub>f</sub> =20mA
Spectral Line Half-Width	Δλ	nm	I <sub>f</sub> =20mA
Reverse Current Any Chip	I <sub>r</sub>	μA	V <sub>r</sub> =5V
Luminous Intensity Matching Ratio	IV-M		



### Typical Electro-Optical Characteristics Curve

E CHIP

Fig.1 Forward current vs. Forward Voltage

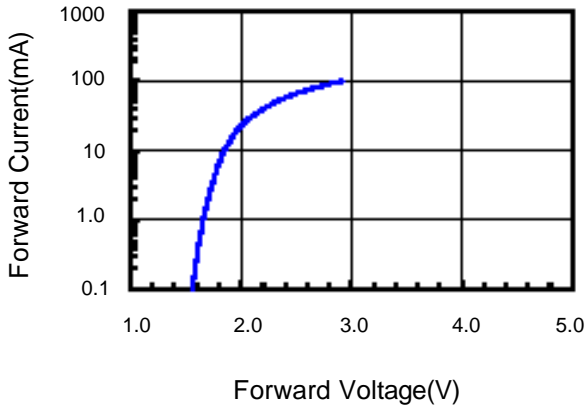


Fig.2 Relative Intensity vs. Forward Current

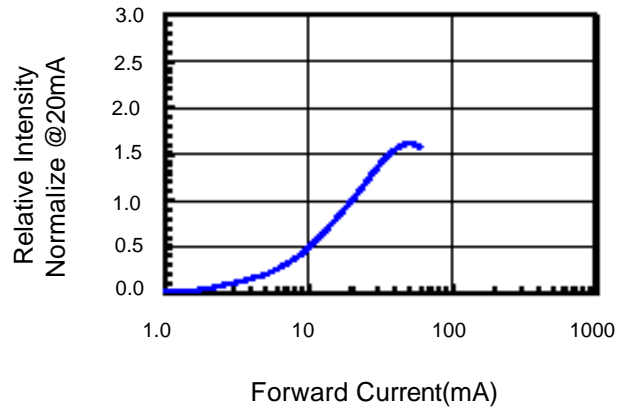


Fig.3 Forward Voltage vs. Temperature

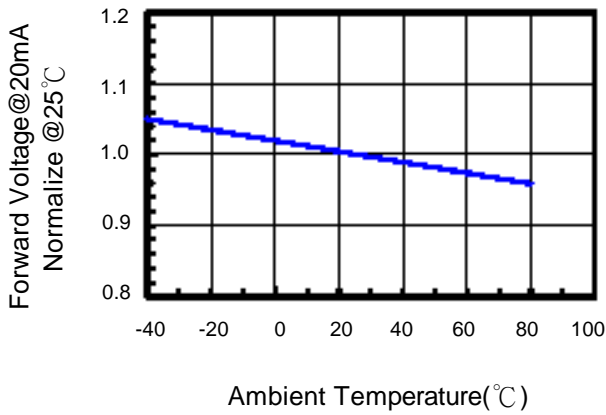


Fig.4 Relative Intensity vs. Temperature

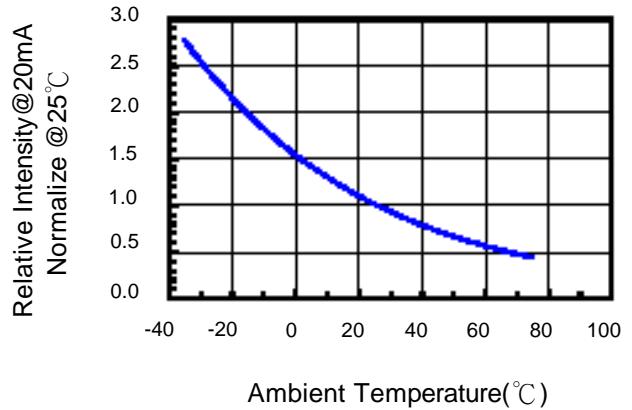
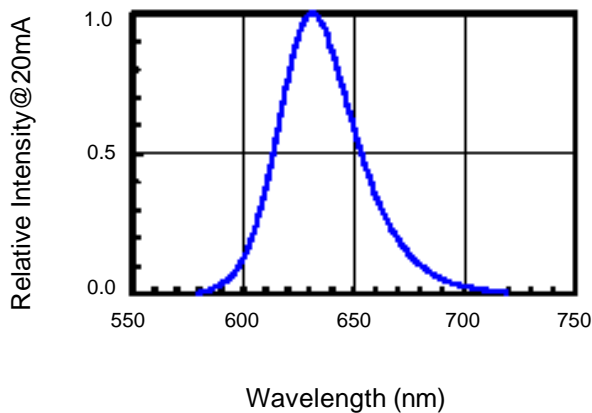


Fig.5 Relative Intensity vs. Wavelength





### Typical Electro-Optical Characteristics Curve

#### G CHIP

Fig.1 Forward current vs. Forward Voltage

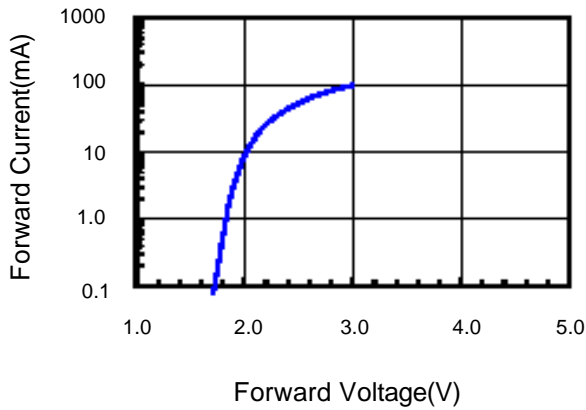


Fig.2 Relative Intensity vs. Forward Current

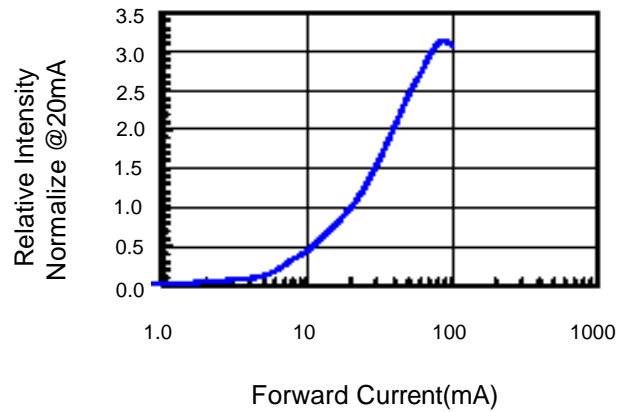


Fig.3 Forward Voltage vs. Temperature

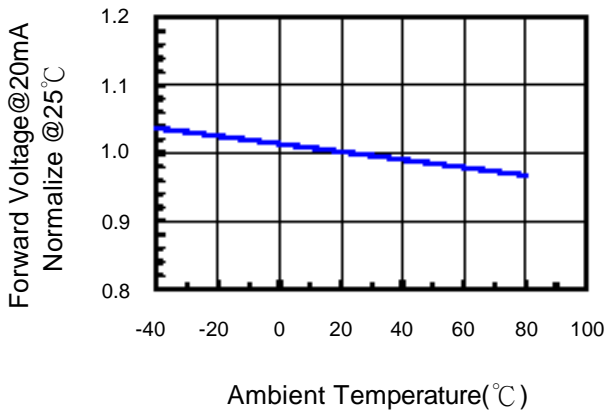


Fig.4 Relative Intensity vs. Temperature

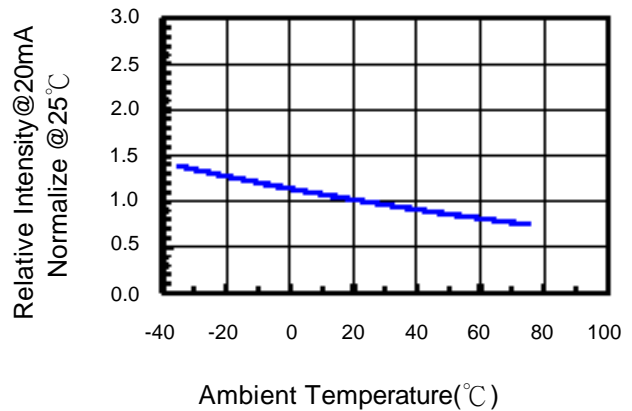
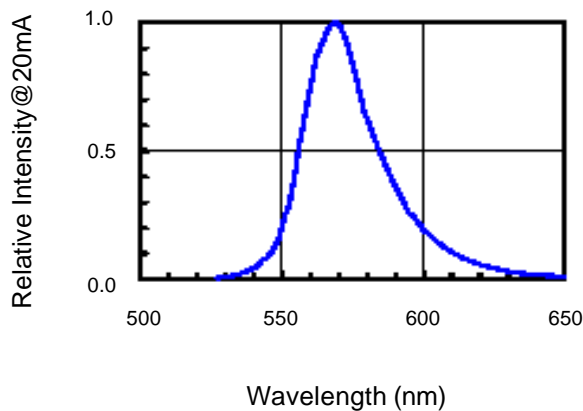


Fig.5 Relative Intensity vs. Wavelength







### Soldering Condition(Pb-Free)

#### 1.Iron:

Soldering Iron:30W Max

Temperature 350° C Max

Soldering Time:3 Seconds Max(One time only)

Distance:Solder Temperature 1/16 Inch Below Seating  
Plane For 3 Seconds At 260° C

#### 2.Wave Soldering Profile

Dip Soldering

Preheat: 120° C Max

Preheat time: 60seconds Max

Ramp-up

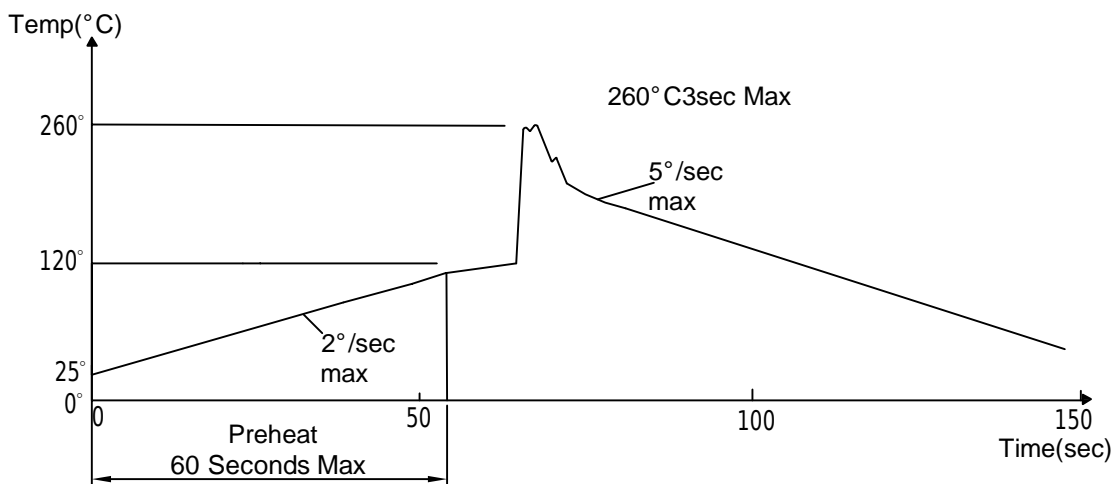
2° C/sec(max)

Ramp-Down:-5° C/sec(max)

Solder Bath:260° C Max

Dipping Time:3 seconds Max

Distance:Solder Temperature 1/16 Inch Below Seating  
Plane For 3 Seconds At 260° C



Note: 1.Wave solder should not be made more than one time.  
2.You can just only select one of the soldering conditions as above.



Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of detemining the resistance of a part in electrical and themal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 °C±5°C 2.RH=90%~95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 °C±5°C&-40°C±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 °C±5°C 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 °C±5°C 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2